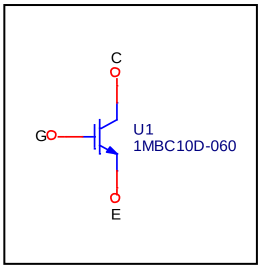
Device Modeling Report

COMPONENTS: Insulated Gate Bipolar Transistor (IGBT)
PART NUMBER: 1MBC10D-060
MANUFACTURER: FUJI ELECTRIC

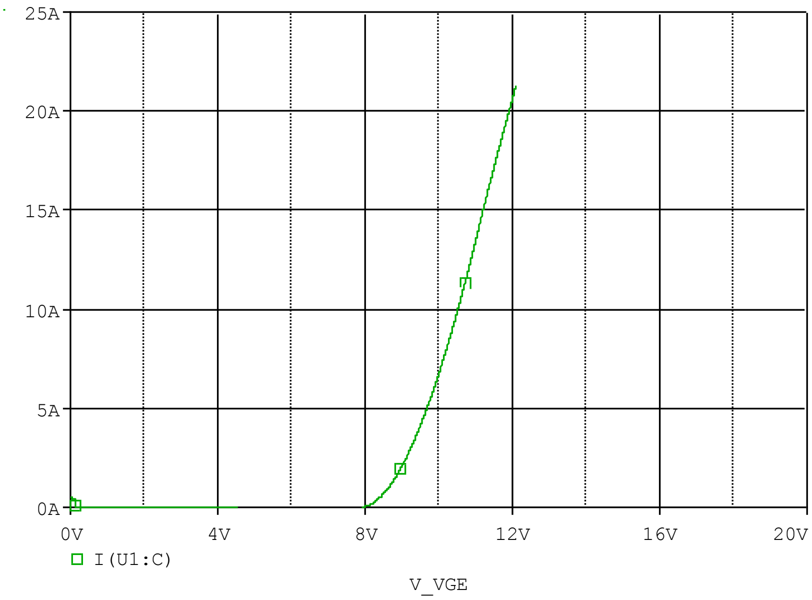
Bee Technologies Inc.

Circuit Configuration

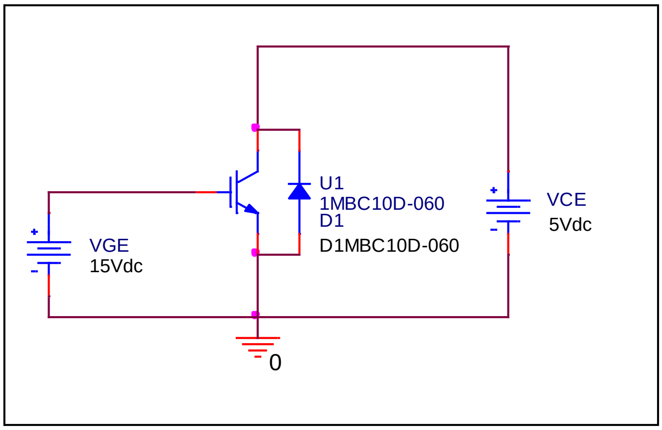


Transfer Characteristics

Circuit Simulation result

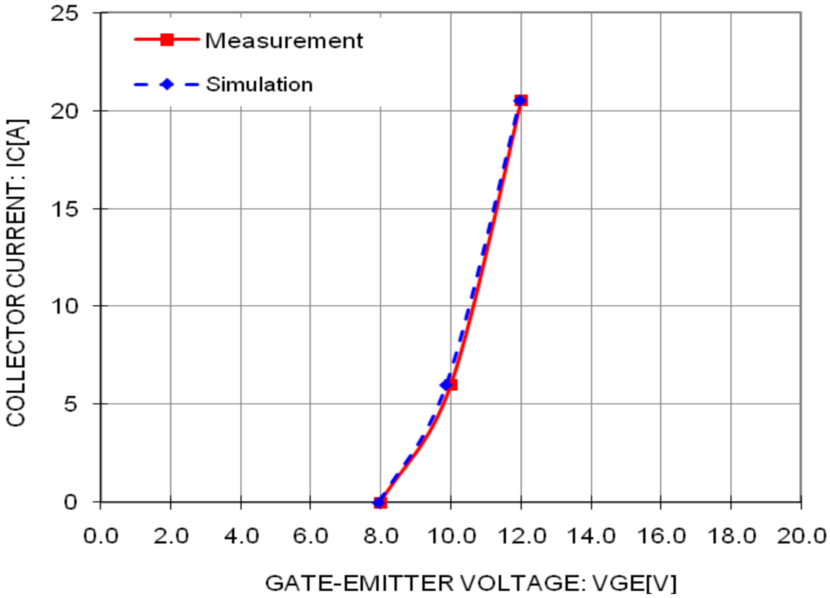


Evaluation circuit



Comparison Graph

Simulation result



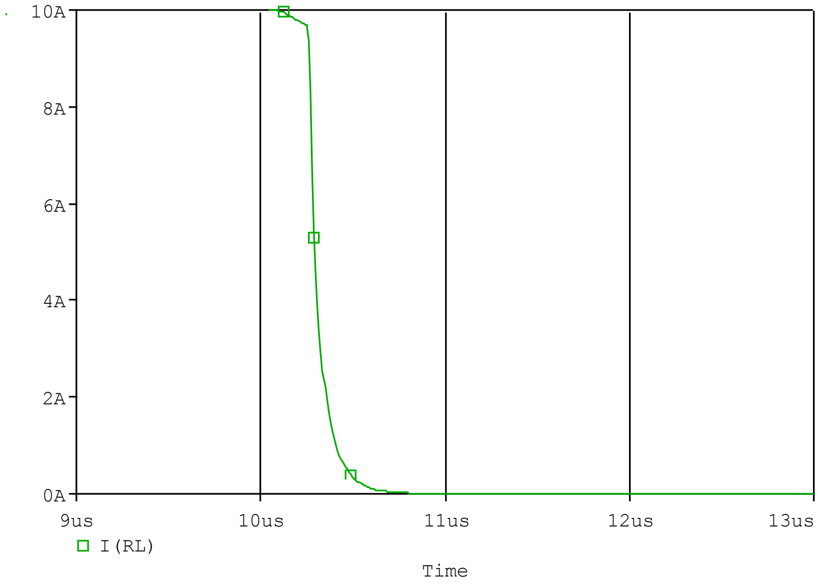
Comparison table

Test condition: V_{CE} =5 (V)

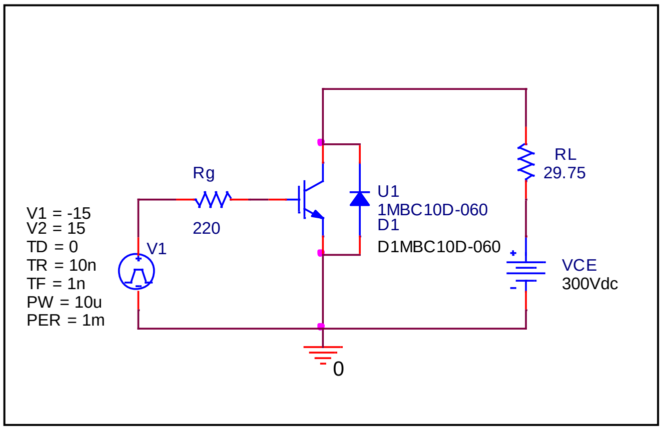
IC (A)	VGE (V)		%Error
	Measurement	Simulation	
0.000	8.000	7.950	-0.63
6.000	10.000	9.870	-1.30
20.500	12.000	11.983	-0.14

Fall Time Characteristics

Circuit Simulation result



Evaluation circuit

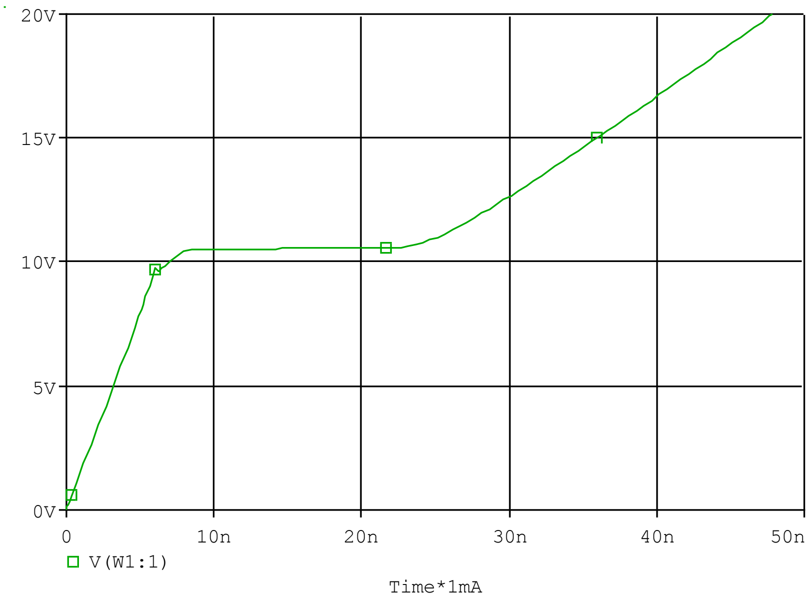


Test condition: Ic=10 (A), Vcc=300 (V)

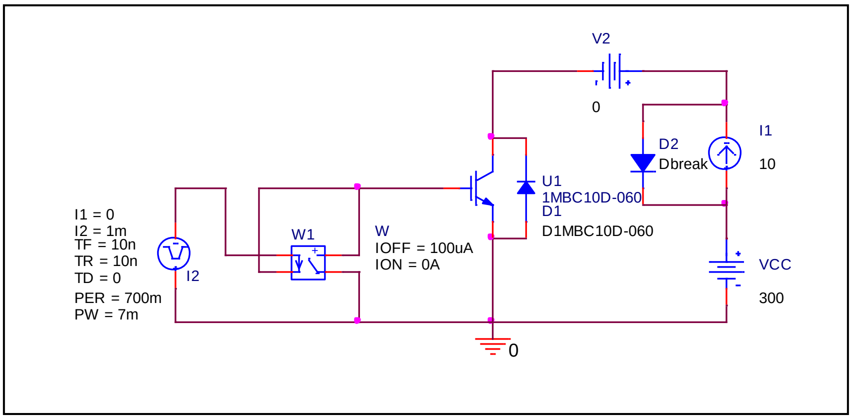
Parameter	Unit	Measurement	Simulation	%Error
tf	us	0.150	0.148	-1.33

Gate Charge Characteristics

Circuit Simulation result



Evaluation circuit

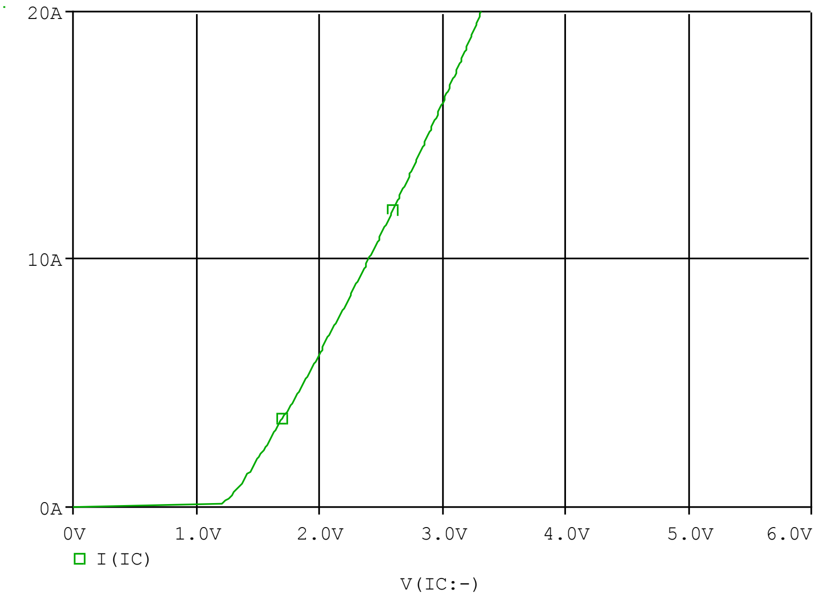


Test condition: V_{CC}=300 (V), I_{C}=10 (A), V_{GE}=15 (V)

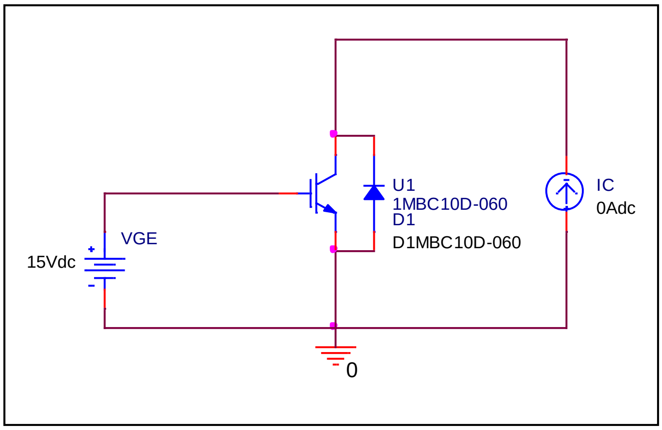
Parameter	Unit	Measurement	Simulation	%Error
Qge	nc	6.000	6.054	0.90
Qgc	nc	17.500	16.829	-3.83
Qg	nc	35.600	35.952	0.99

Saturation Characteristics

Circuit Simulation result

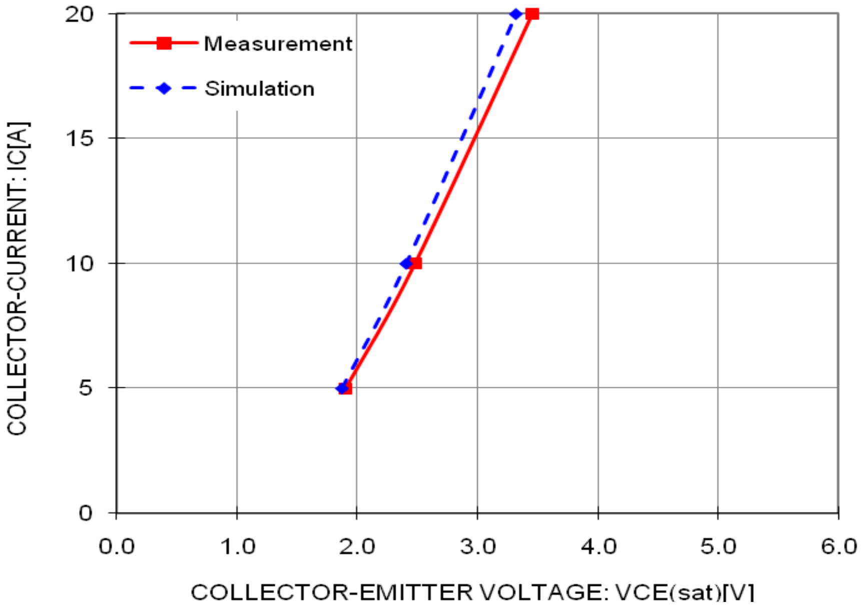


Evaluation circuit



Comparison Graph

Simulation result



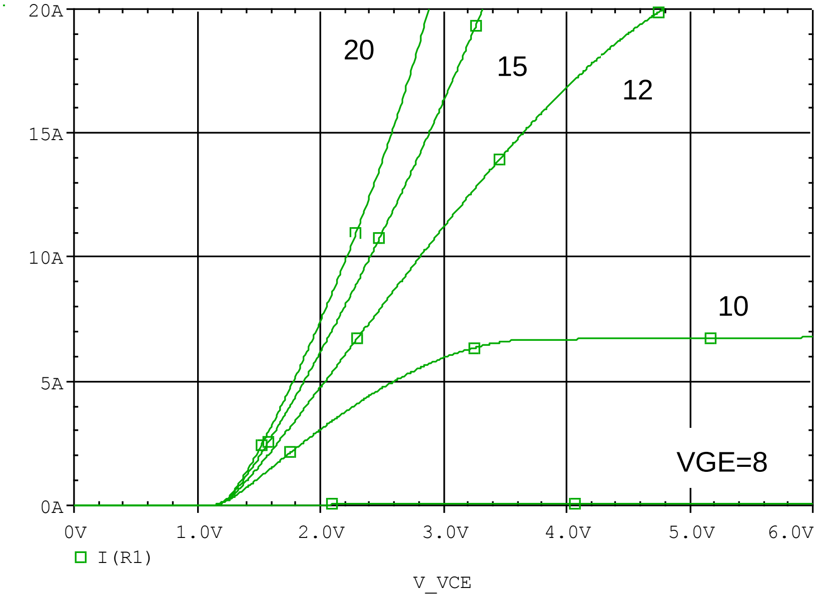
Comparison table

Test condition: VGE =15 (V)

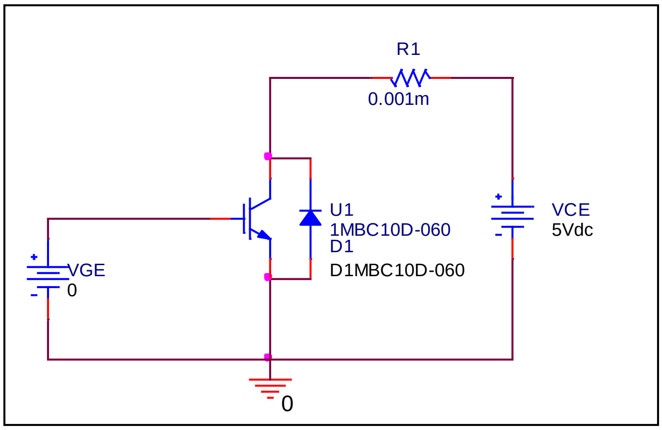
Ic(A)	VCE (V)		%Error
	Measurement	Simulation	
5	1.900	1.869	-1.63
10	2.475	2.404	-2.87
20	3.450	3.319	-3.80

Output Characteristics

Circuit Simulation result

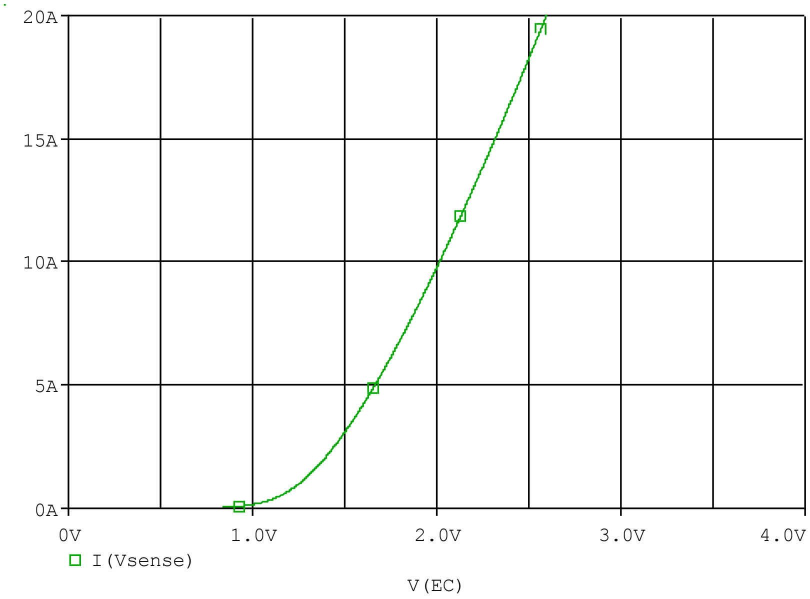


Evaluation circuit

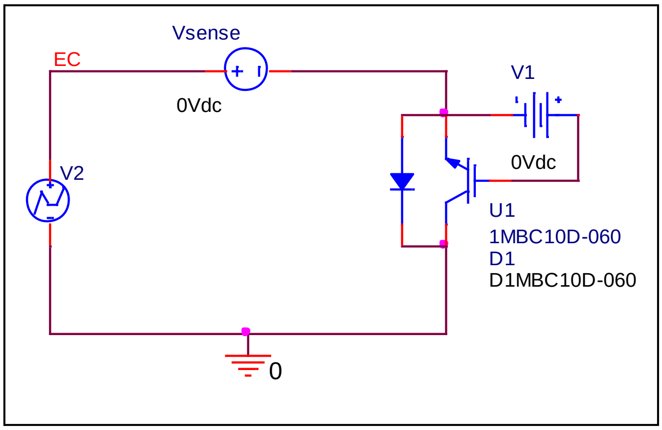


FWD Forward Current Characteristics

Circuit Simulation result

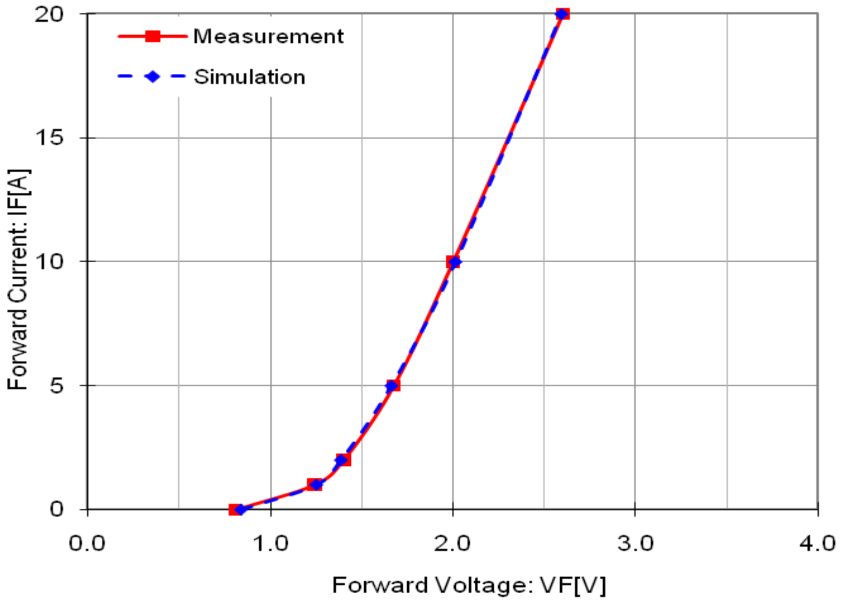


Evaluation circuit



Comparison Graph

Simulation result

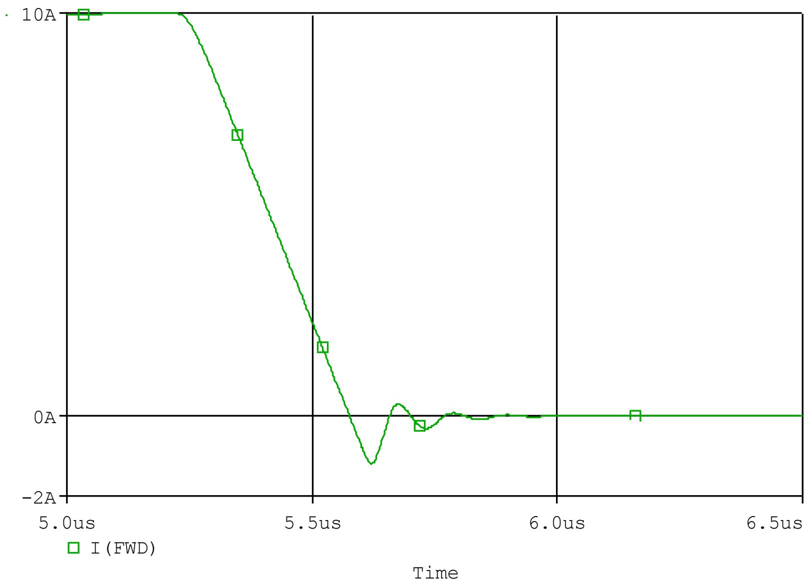


Comparison table

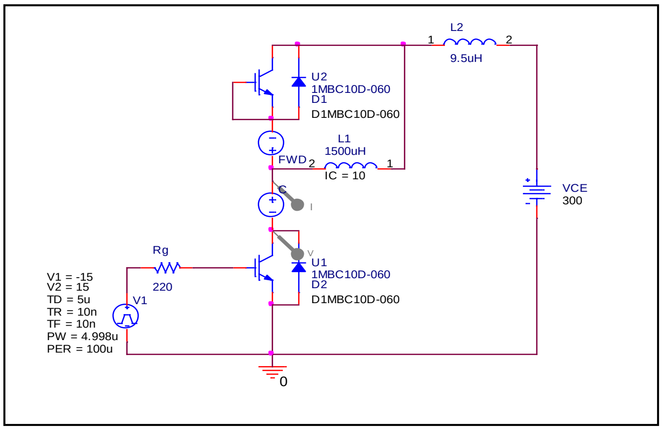
IF(A)	VF (V)		%Error
	Measurement	Simulation	
0	0.810	0.840	3.70
1	1.240	1.253	1.01
2	1.400	1.388	-0.86
5	1.675	1.664	-0.64
10	2.000	2.015	0.72
20	2.600	2.596	-0.15

Reverse Recovery Characteristics

Circuit Simulation result



Evaluation circuit



Test condition: VCC=300 (V) ,IC=10 (A) ,-dit/dt=30A/usec.

Parameter	Unit	Measurement	Simulation	%Error
trr	nsec	125.000	79.392	-36.49
Irr	A	1.200	1.197	-0.25